### RECTIFIER, up to 1kV, 2A, 2µs

1N5614 S<sub>2</sub>M 1N5616 **S4M** 1N5618 S<sub>6</sub>M 1N5620 S8M 1N5622 S<sub>0</sub>M

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TEL:805-498-2111 FAX:805-498-3804 WEB:http://www.semtech.com

#### QUICK REFERENCE AXIAL LEADED HERMETICALLY SEALED DATA STANDARD RECOVERY RECTIFIER DIODE

- = 2.0A
- $t_{rr} = 2\mu S$
- $V_F = 1.1V$
- $V_R = 200 1000V$  Low reverse leakage current
  - Hermetically sealed in Metoxilite fused metal oxide
  - Good thermal shock resistance
  - Low forward voltage drop
  - Avalanche capability.

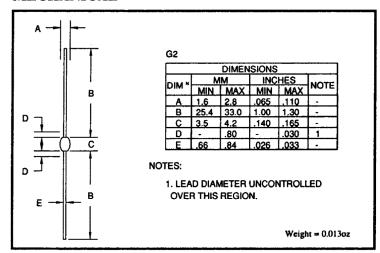
## ABSOLUTE MAXIMUM RATINGS (@ 25°C unless otherwise specified)

	Symbol	1N5614 1N5616 1N5618 1N5620 1N5622 Unit S2M S4M S6M S8M S0M
Working reverse voltage	V <sub>RWM</sub>	200 400 600 800 1000 V
Repetitive reverse voltage	V <sub>RRM</sub>	200 400 600 800 1000 V
Average forward current (@ 55°C, lead length 0.375")	I <sub>F(AV)</sub>	2.0 — A
Repetitive surge current (@ 55°C in free air, lead length 0.375")	I <sub>FRM</sub>	→ 10 → A
Non-repetitive surge current $(t_p = 8.3 \text{mS}, @ V_R \& T_{jmax})$	I <sub>FSM</sub>	→ 30 → A
Storage temperature range	TSTG	← -65 to +175 → °C
Operating temperature range	TOP	← -65 to +175 — °C

These products are qualified to MIL-PRF-19500/427 and are preferred parts as listed in MIL-STD-701. They can be supplied fully released as JAN, JANTX, JANTXV and JANS versions.

These products are available in Europe to DEF STAN 59-61 (PART 80)/029 to F and FX levels.

### **MECHANICAL**





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# CHARACTERISTICS (@ 25°C unless otherwise specified)

	Symbol	1N5614 1N5616 1N5618 1N5620 1N5622 S2M S4M S6M S8M S0M	Unit
Average forward current (sine wave) - max. pcb mounted; T <sub>A</sub> = 55°C - max. L = 3/8"; T <sub>L</sub> = 55°C	I <sub>F(AV)</sub> I <sub>F(AV)</sub>	1.0	A A
$I^2$ t for fusing (t = 8.3mS) max.	I <sup>2</sup> t	5.0	A <sup>2</sup> S
Forward voltage drop max. @ $I_F = 1.0A$ , $T_j = 25^{\circ}$ C	$V_{\mathrm{F}}$	1.1	v
Reverse current max. @ $V_{RWM}$ , $T_j = 25^{\circ}C$ @ $V_{RWM}$ , $T_j = 100^{\circ}C$	I <sub>R</sub> I <sub>R</sub>	0.5	μΑ μΑ
Reverse recovery time max. 0.5A I <sub>F</sub> to 1.0A I <sub>R</sub> . Recovers to 0.25A I <sub>RR</sub> .	t <sub>rr</sub>	← 2.0 ←	μS
Junction capacitance typ. $@V_R = 5V$ , $f = 1MHz$	Cj	23	ρF
Thermal resistance - junction to lead Lead length = 0.375" Lead length = 0"	R <sub>0JL</sub> R <sub>0JL</sub>		°C/W °C/W
Thermal resistance - junction to amb. on 0.06" thick pcb. 1 oz. copper.	R <sub>0JA</sub>	<b>←</b> 95 −	°C/W

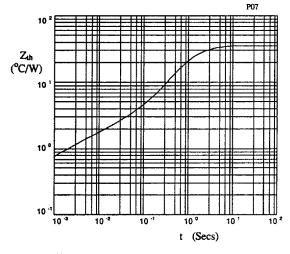


Fig 1. Transient thermal impedance characteristic.

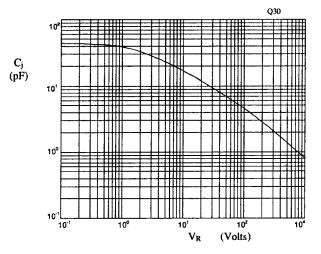


Fig 2. Typical junction capacitance as a function of reverse voltage.



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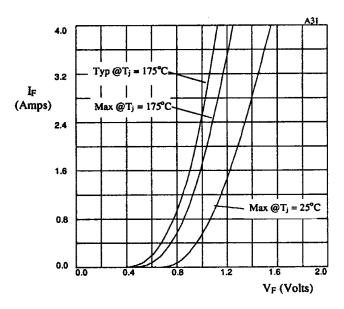


Fig 3. Forward voltage drop as a function of forward current.

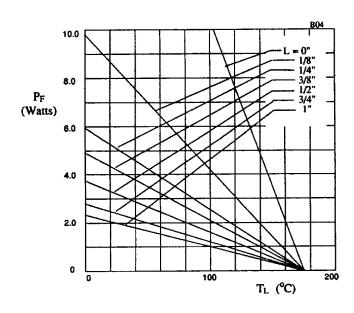


Fig 4. Maximum power versus lead temperature.

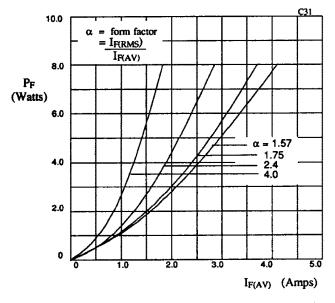


Fig 5. Forward power dissipation as a function of forward current, for sinusoidal operation.

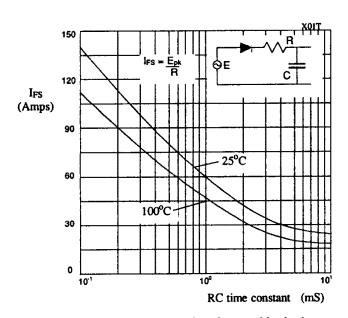


Fig 6. Maximum ratings for capacitive loads.